

N-channel TrenchMOS standard level FET 11 September 2012

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in a SOT226 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant •
- Repetitive avalanche rated •
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C •

1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering •
- Motors, lamps and solenoid control •
- Start-Stop micro-hybrid applications
- Transmission control •
- Ultra high performance power switching •

1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	-	120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	349	W
Static chara	acteristics	1	I				
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11		-	1.5	1.8	mΩ
Dynamic cl	naracteristics	·					
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 25 A; V _{DS} = 32 V; Fig. 13; Fig. 14		-	48.2	-	nC

Quick reference data Table 1

[1] Continuous current is limited by package.

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G - C - C - C - C - C - C - C - C - C -
mb	D	mounting base; connected to drain	I 2 3 I 2PAK (SOT226)	mbb076 S

3. Ordering information

Table 3. Ordering information						
Type number Package						
	Name	Description	Version			
BUK7E1R8-40E	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226			

4. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7E1R8-40E	BUK7E1R8-40E

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	40	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	120	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	120	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	1278	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	349	W
T _{stg}	storage temperature			-55	175	°C

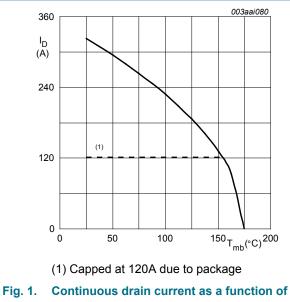
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Symbol	Parameter	Conditions		Min	Мах	Unit
Tj	junction temperature			-55	175	°C
Source-drai	in diode					,
I _S	source current	T _{mb} = 25 °C	[1]	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	1278	А
Avalanche r	ruggedness					,
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 120 \text{ A}; \text{V}_{sup} \leq 40 \text{V}; \text{R}_{GS} = 50 \Omega; \\ \text{V}_{GS} &= 10 \text{V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. 3} \end{split}$	[2][3]	-	1021	mJ

[1] Continuous current is limited by package.

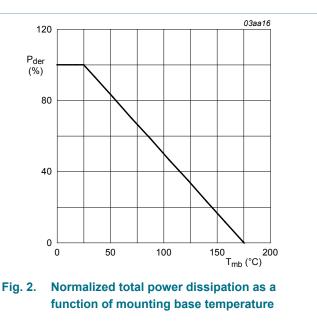
[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Refer to application note AN10273 for further information.



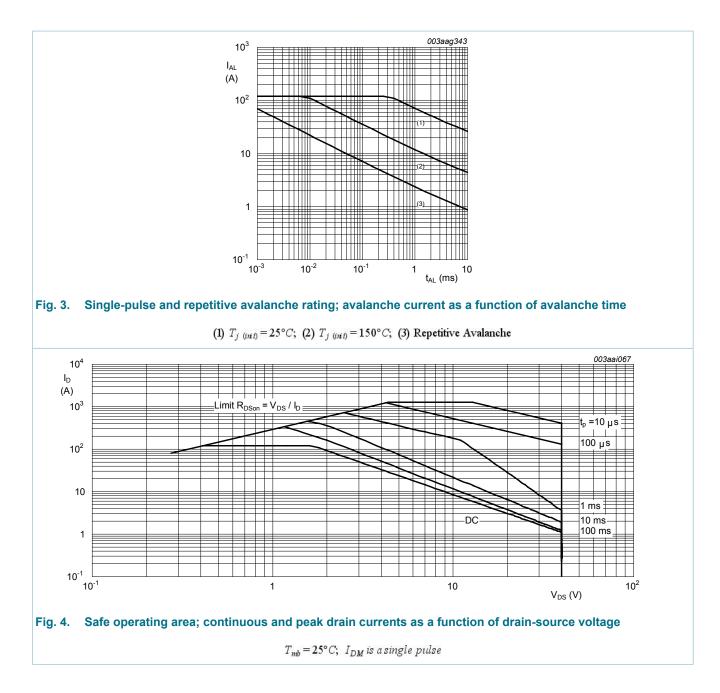
mounting base temperature

 $V_{GS} \ge 10V$



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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6. Thermal characteristics

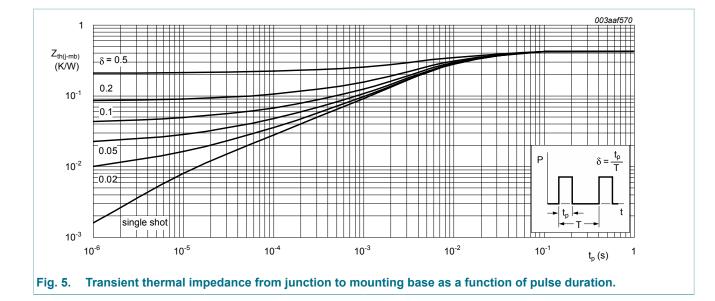
Table 6. T	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.43	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in still air	-	65	-	K/W

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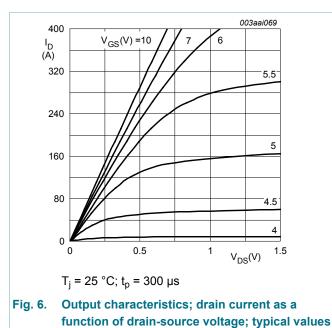


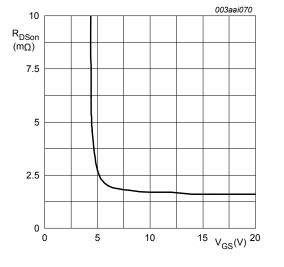
Characteristics 7.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·	I			_
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	40	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	36	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	4.5	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 10	1	-	-	V
I _{DSS}	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C	-	0.25	3	μA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	1.5	1.8	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	3.4	mΩ
Dynamic ch	naracteristics	· · ·	'			
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	145	-	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	35.7	-	nC
Q _{GD}	gate-drain charge	1	-	48.2	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	8500	11340	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	1620	1950	pF
C _{rss}	reverse transfer capacitance		-	985	1350	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V;	-	42	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	60	-	ns
t _{d(off)}	turn-off delay time		-	121	-	ns
t _f	fall time		-	83	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
		from drain lead 6mm from package to centre of die	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-dra	in diode	· · · ·	1			
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; Fig. 16	-	0.77	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	56	-	ns
Q _r	recovered charge	V _{DS} = 25 V	-	94	-	nC



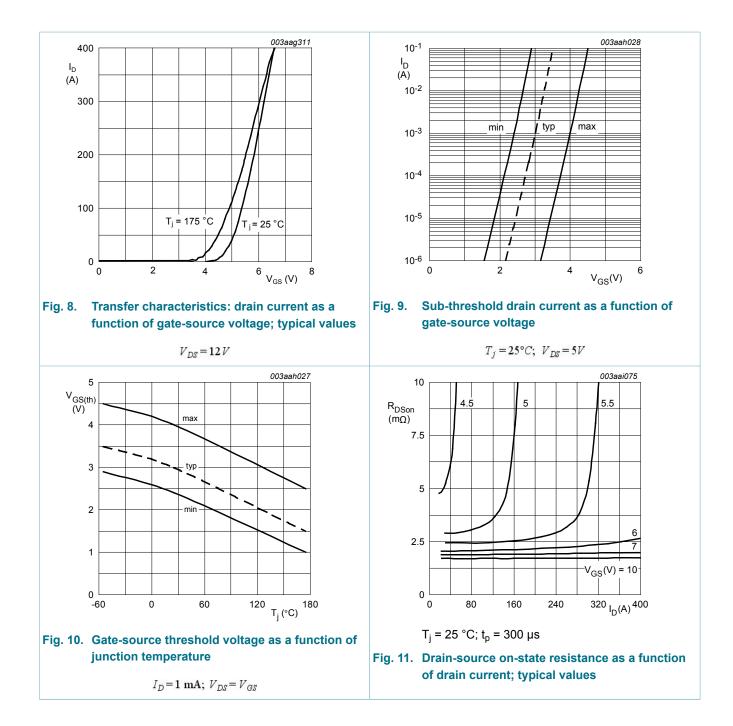




 $T_j = 25^{\circ}C; I_D = 25A$

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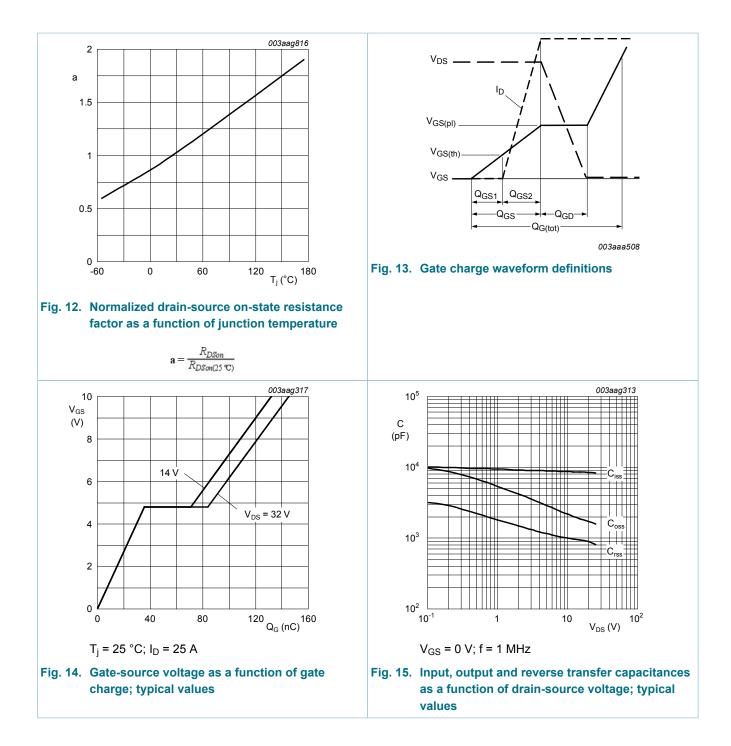
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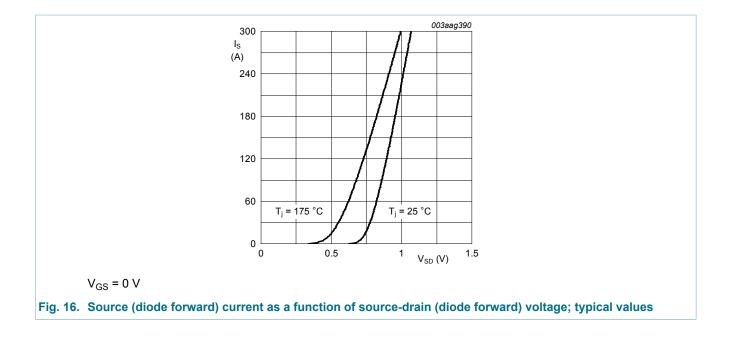
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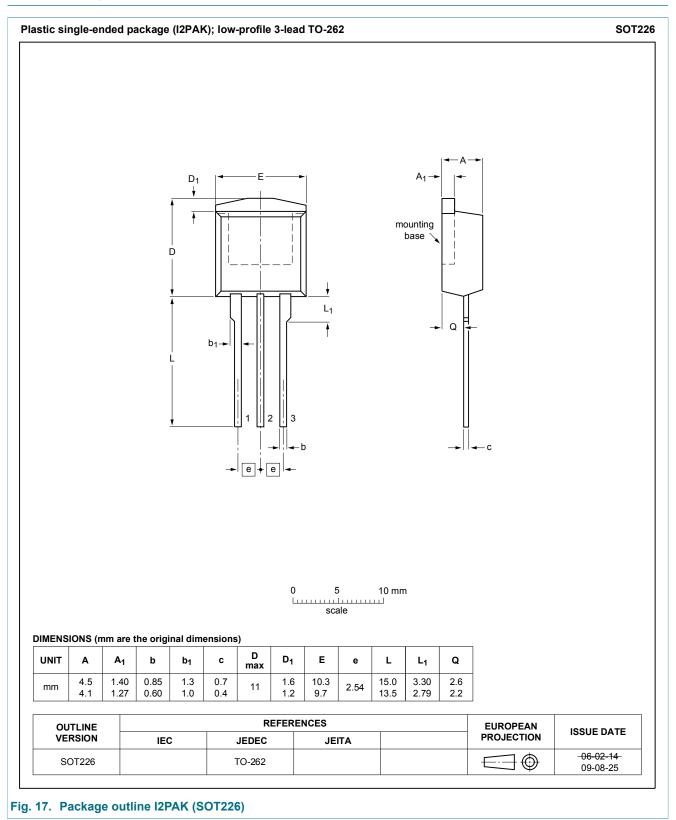
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8. Package outline



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9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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